

	Type	L #	Hits	Search Text	DBs
1	BRS	L43	71695	method near5 memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
2	BRS	L44	673	(metal near1 interconnect) near5 (substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
3	BRS	L45	80	(memory adj1 cell adj1 storage) near5 (voltage or current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
4	BRS	L46	16	43 and 44	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
5	BRS	L47	0	45 and 46	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
6	BRS	L48	37	43 and 45	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
7	BRS	L49	0	44 and 48	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
8	BRS	L50	17405	(memory adj1 cell) near5 (voltage or current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
9	BRS	L52	0	44 and 45	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
10	BRS	L51	3	46 and 50	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
11	BRS	L53	3	44 and 50	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
12	BRS	L54	583	(memory adj1 cell) near5 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
13	BRS	L55	0	44 and 54	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
14	BRS	L56	351	43 and 54	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
15	BRS	L57	0	56 and (interconnect near7 substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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16	BRS	L58	0	56 and (interconnect near10 substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
17	BRS	L59	0	56 and (metal adj1 interconnect)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
18	BRS	L60	24	56 and (interconnect)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
19	BRS	L61	120974	438/\$.ccls.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
20	BRS	L62	4369	43 and 61	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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21	BRS	L63	8	44 and 62	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
22	BRS	L64	2	50 and 63	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
23	BRS	L65	504	438/618.ccls.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
24	BRS	L66	77	65 and metal adj1 interconnect	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
25	BRS	L67	1304	(memory adj1 cell near3 transistor) near5 substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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26	BRS	L68	29	54 and 67	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
27	BRS	L69	3	(memory adj1 cell near3 device\$1) near5 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
28	BRS	L70	13	67 and metal adj1 interconnect	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
29	BRS	L71	1538	method near5 non-volatile near3 memory.ti.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
30	BRS	L72	7580	memory adj1 cell near5 substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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31	BRS	L73	0	metal adj1 interconnect near5 (substrate and memory adj1 cell)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
32	BRS	L74	589	metal adj1 interconnect near5 (substrate or memory adj1 cell)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
33	BRS	L76	0	74 and 75	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
34	BRS	L77	0	71 and 74	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
35	BRS	L78	11	72 and 74	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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36	BRS	L75	127	71 and 72	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
37	BRS	L79	9	5761115.pn. or 5896312.pn. or 5914893.pn. or 6084976.pn.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
38	BRS	L80	50326	365/\$.cc1s.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
39	BRS	L81	22832	80 and memory adj1 cell	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
40	BRS	L82	2614	81 and non-volatile adj1 memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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41	BRS	L83	1	82 and (metal adj1 interconnect) near5 (substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
42	BRS	L84	12471	365/143-182.ccls.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
43	BRS	L85	602	84 and non-volatile adj1 memory	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
44	BRS	L86	0	85 and first adj1 memory adj1 cell adj1 electrode	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
45	BRS	L87	4	85 and memory adj1 cell adj1 electrode	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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46	BRS	L88	14	85 and metal adj1 interconnect	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
47	BRS	L89	18	85 and memory adj1 cell adj1 storage	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
48	BRS	L90	2	(plurality near1 metal near1 interconnect) near5 (semiconductor adj1 substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
49	BRS	L91	181	(metal near1 interconnect) near5 (semiconductor adj1 substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
50	BRS	L92	51	metal near10 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

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51	BRS	L93	0	91 and 92	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
52	BRS	L94	2210	(metal oe electrode\$1) near10 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
53	BRS	L95	2184	(metal or electrode\$1) near10 (voltage and current)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
54	BRS	L96	0	91 and 95	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
55	BRS	L97	19226	(metal or electrode\$1) near10 (voltage and current or resistance)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
56	BRS	L98	23	91 and 97	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	U	1	Document ID	Title	Current OR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6350651 B1	Method for making flash memory with UV opaque passivation layer	438/257
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5702988 A	Blending integrated circuit technology	438/238
3	<input type="checkbox"/>	<input type="checkbox"/>	US 5659511 A	Method for measuring the current leakage of a dynamic random access memory capacitive junction	365/201

	U	1	Document ID	Title	Current OR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6281110 B1	Method for making an integrated circuit including deuterium annealing of metal interconnect layers	438/622
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6277764 B1	Interlayered dielectric layer of semiconductor device and method of manufacturing the same	438/763